

SIDDHARTH INSTITUTE OF ENGINEERING & TECHNOLOGY:: PUTTUR
(AUTONOMOUS)

B.Tech I Year I Semester Regular Examinations February-2024
ENGINEERING PHYSICS

(Common to EEE, ECE & CSIT)

Time: 3 Hours

Max. Marks: 70

PART-A

(Answer all the Questions 10 x 2 = 200 Marks)

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|---|---|--|-----|----|----|
| 1 | a | Write any two differences between Fraunhofer and Fresnel diffraction | CO1 | L2 | 2M |
| | b | Define Resolving Power of Grating. | CO1 | L1 | 2M |
| | c | Define Lattice parameters. | CO2 | L1 | 2M |
| | d | Define Bragg's condition for X-Ray diffraction. | CO2 | L1 | 2M |
| | e | Define dielectric constant. | CO3 | L1 | 2M |
| | f | Define magnetic susceptibility and magnetization. | CO4 | L1 | 2M |
| | g | Define mean free path. | CO5 | L1 | 2M |
| | h | Write any two merits of classical free electron theory. | CO5 | L2 | 2M |
| | i | Define Intrinsic and Extrinsic semiconductors. | CO6 | L1 | 2M |
| | j | What are the applications of Hall effect | CO6 | L1 | 2M |

PART-B

(Answer all Five Units 5 x 10 = 50 Marks)

UNIT-I

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|---|---|---|-----|----|----|
| 2 | a | Describe the formation of Newton's ring with necessary theory with relevant diagrams. | CO1 | L3 | 7M |
| | b | Calculate the thickness of Half-Wave plate, given that $\mu_e = 1.533$, $\mu_o = 1.544$ and $\lambda = 5000 \text{ \AA}$. | CO1 | L4 | 3M |

OR

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|---|---|---|-----|----|-----|
| 3 | a | Define Diffraction and Explain about Fraunhofer diffraction due to a single slit, with intensity distribution curves. | CO2 | L3 | 10M |
|---|---|---|-----|----|-----|

UNIT-II

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|---|---|--|-----|----|-----|
| 4 | a | Show that Face centered cubic crystal structure has more closely packed structure than SC and BCC. | CO2 | L2 | 10M |
|---|---|--|-----|----|-----|

OR

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|---|---|--|-----|----|----|
| 5 | a | Explain how crystal structure determined by Laue X-Ray diffraction method. | CO2 | L2 | 7M |
| | b | What are the advantages of Laue X-Ray diffraction method? | CO2 | L1 | 3M |

UNIT-III

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|---|---|---|-----|----|----|
| 6 | a | Explain the different types of polarizations. | CO3 | L3 | 4M |
| | b | Derive the expression for electronic polarizability, α_e in dielectrics. | CO3 | L4 | 6M |

OR

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|---|---|---|-----|----|-----|
| 7 | a | Describe the classification of magnetic materials based magnetic moments. | CO4 | L1 | 10M |
|---|---|---|-----|----|-----|

UNIT-IV

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|---|---|---|-----|----|----|
| 8 | a | Derive the expression for de Broglie wavelength | CO5 | L3 | 6M |
| | b | Explain the properties of matter waves. | CO5 | L2 | 4M |

OR

- 9 a** Derive an expression for electrical conductivity in a metal by quantum free electron theory. **CO5 L3 7M**
- b** What are the advantages of quantum free electron theory over classical free electron theory? **CO5 L1 3M**

UNIT-V

- 10 a** Derive Einstein's relation for charge carriers in semiconductor. **CO6 L2 5M**
- b** Explain about intrinsic and extrinsic semiconductors. **CO6 L2 5M**

OR

- 11 a** Explain Hall Effect in semiconductors. **CO6 L2 6M**
- b** If RH of a specimen is $3.66 \times 10^{-4} \text{ m}^3 \text{ c}^{-1}$. Its resistivity is $8.93 \times 10^{-3} \Omega\text{-m}$. Find mobility and electron concentration. **CO6 L3 4M**

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